

General Purpose Amplifier Transistor

NPN Silicon Surface Mount

MSD1819A-RT1G, NSVMSD1819A-RT1G

This NPN Silicon Epitaxial Planar Transistor is designed for general purpose amplifier applications. This device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

Features

- High h_{FE}, 210-460
- Low $V_{CE(sat)}$, < 0.5 V
- Moisture Sensitivity Level 1
- ESD Protection:
 - ♦ Human Body Model > 4000 V
 - ♦ Machine Model > 400 V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25 °C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	60	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current - Continuous	I _C	100	mAdc
Collector Current - Peak	I _{C(P)}	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P_{D}	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

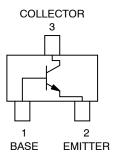
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

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SC-70 (SOT-323) **CASE 419** STYLE 3



MARKING DIAGRAM



= Device Code = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVMSD1819A-RT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = 2.0 mAdc, I _B = 0)	V _{(BR)CEO}	50	_	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _{(BR)CBO}	60	_	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu Adc, I_E = 0$)	V _{(BR)EBO}	7.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	0.1	μΑ
Collector-Emitter Cutoff Current (V _{CE} = 10 Vdc, I _B = 0)	I _{CEO}	-	0.1	μΑ
DC Current Gain (Note 2) $ (V_{CE} = 10 \text{ Vdc}, I_C = 2.0 \text{ mAdc}) $ $ (V_{CE} = 2.0 \text{ Vdc}, I_C = 100 \text{ mAdc}) $	h _{FE1} h _{FE2}	210 90	340 -	-
Collector-Emitter Saturation Voltage (Note 2) ($I_C = 100 \text{ mAdc}$, $I_B = 10 \text{ mAdc}$)	V _{CE(sat)}	_	0.5	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Pulse Test: Pulse Width \leq 300 μ s, D.C. \leq 2%.

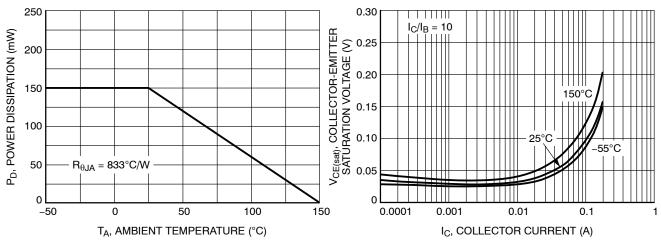


Figure 1. Derating Curve

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

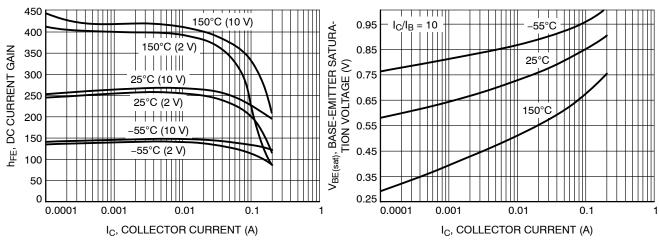
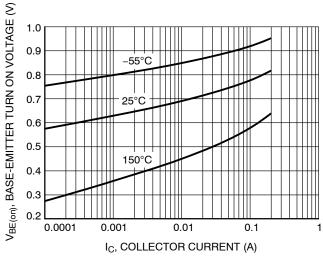


Figure 3. DC Current Gain vs. Collector Current

Figure 4. Base Emitter Saturation Voltage vs. Collector Current

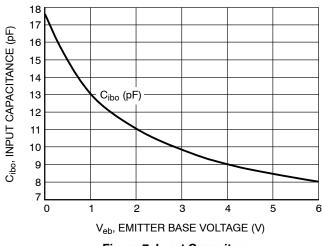
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V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) 1.2 1.0 = 100 mA 10 mA 50 mA 0.8 0.6 0.4 0.2 0 0.000001 0.00001 0.0001 0.001 0.01 IB, BASE CURRENT (A)

Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

Figure 6. Collector Saturation Region



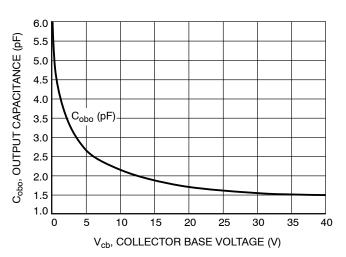


Figure 7. Input Capacitance

Figure 8. Output Capacitance

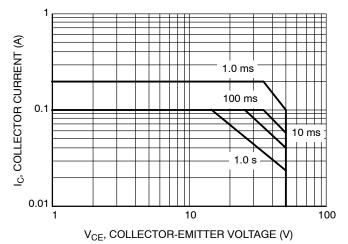


Figure 9. Safe Operating Area

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REVISION HISTORY

Revision	Description of Changes	Date
11	Rebranded the Data Sheet to onsemi format.	10/15/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.







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DATE 11 OCT 2022

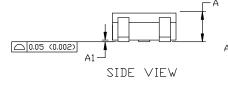
NOTES:

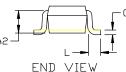
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

SCALE 4:1

TOP VIEW





GENERIC MARKING DIAGRAM

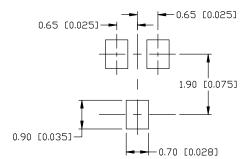


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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